

SPECIFICATION

Please amend Page 8, Line 7, of the Specification:

A preferred non-linear device of this invention is a metal-insulator-metal (MIM) diode. A MIM diode was produced as follows: First, tantalum oxide was produced by taking 1 g of tantalum powder (<2micron, Alfa Aesar) was mixed with 1 cc water in a ceramic bowl. The mixture was placed in an oven ~~in an oven~~ at 150°C for 20 minutes. The mixture was then remixed and placed back in the oven for an additional 15 minutes. Second, a dielectric binder was produced by dissolving 1.0 g of epoxy (0.5 g part A and 0.5 gm part B, Proxy Epoxy Craft, 2 part epoxy) in 5 ml methyl ethyl ketone (MEK). To the epoxy MEK solution was added 1 g of carbon powder (Glassy carbon spherical powder, 10-20 micron, type 1, Alfa-Aesar). Third, MIM composition was then produced by adding 0.5 g of the tantalum oxide powder to the dielectric binder.

Respectfully submitted,



Arnold B. Silverman
Attorney for Applicants
Registration Number 22,614

Telephone: 412-566-2077
E-mail: ipmail@eckertseamans.com